

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE30ND07BS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =6.5A

 $R_{DS(ON)}$ < 29m Ω @ V_{GS} =10V

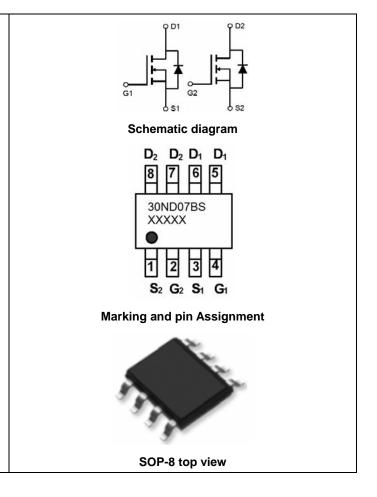
 $R_{DS(ON)}$ <34m Ω @ V_{GS} =4.5V

 $R_{DS(ON)} < 44m\Omega @ V_{GS} = 2.5V$

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30ND07BS	NCE30ND07BS	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

About the American Returning (1A-15 Cultimote Cultion Wilder Hotelay)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage	V _{GS}	±12	V		
Drain Current-Continuous	I _D	6.5	А		
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	4.6	Α		
Pulsed Drain Current	I _{DM}	26	Α		
Maximum Power Dissipation	P _D	2	W		
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$		

Thermal Characteristic

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	85	°C/W

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u> </u>		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±12 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)	<u> </u>		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.6	0.9	1.2	V
		V _{GS} =10V, I _D =5A	-	25	29	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5A	-	27	34	
		V_{GS} =2.5V, I_D =5A	-	33	44	
Forward Transconductance	g FS	V _{DS} =5V,I _D =5A	-	10	-	S
Dynamic Characteristics (Note4)	,		<u> </u>	I		
Input Capacitance	C _{lss}	\\	-	595	-	PF
Output Capacitance	C _{oss}	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	39	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0Winz	-	36	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	3.0	-	nS
Turn-on Rise Time	t _r	V_{DD} =15V, R_L =3 Ω	-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	25	-	nS
Turn-Off Fall Time	t _f		-	3.8	-	nS
Total Gate Charge	Qg	\/ _45\/ _5 \	-	9.3	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =15V, I_{D} =5A, V_{GS} =4.5V	-	1.6	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	2.1	-	nC
Drain-Source Diode Characteristics	<u> </u>		•		-	-
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS} =0 V , I_{S} =5 A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.5	Α

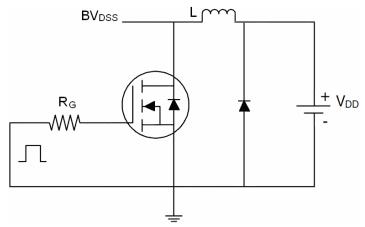
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. Surface Mounted on FR4 Board, t ≤ 10 sec. The current rating is based on the t ≤ 10s thermal resistance rating.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production.

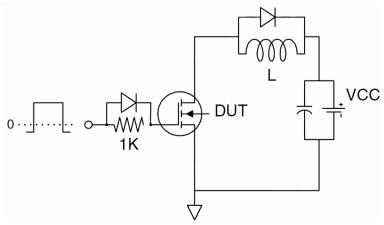


Test Circuit

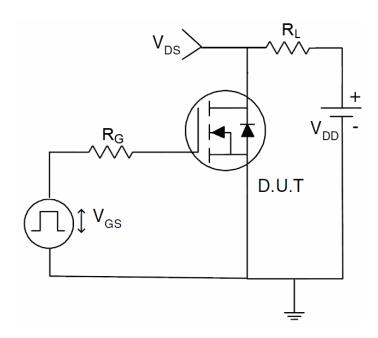
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:

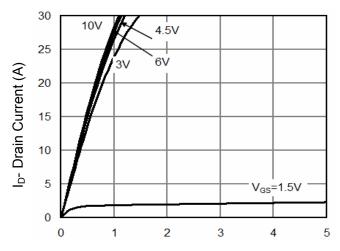




_D- Drain Current (A)

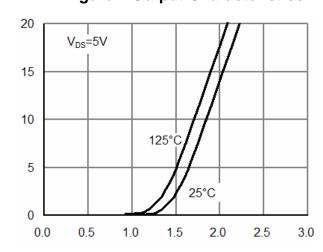
Rdson On-Resistance (m\Omega)

Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

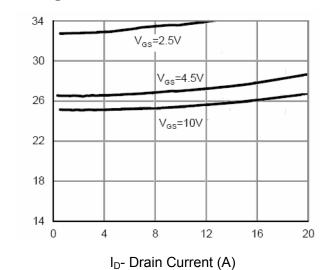


Figure 3 Rdson- Drain Current

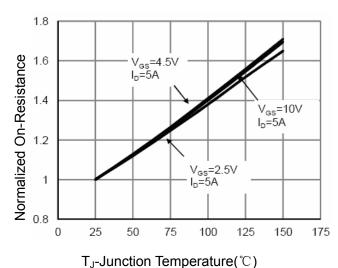


Figure 4 Rdson-JunctionTemperature

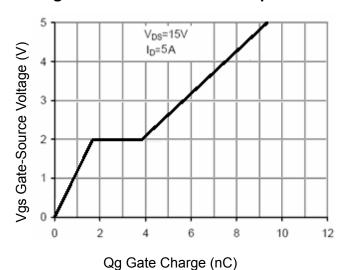
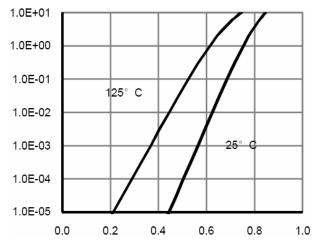


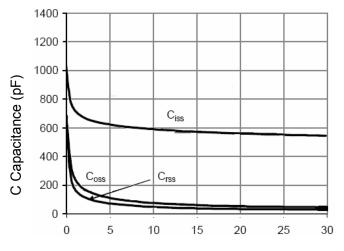
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

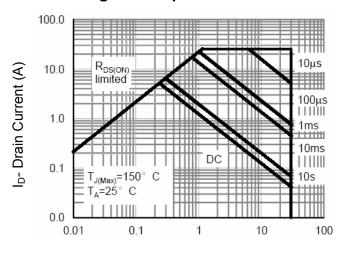
Figure 6 Source- Drain Diode Forward





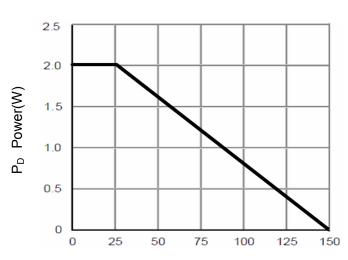
Vds Drain-Source Voltage (V)





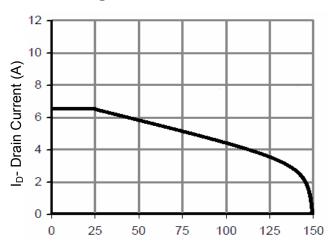
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)

Figure 9 Power Dissipation



 T_J -Junction Temperature($^{\circ}$ C)

Figure 10 Current De-rating

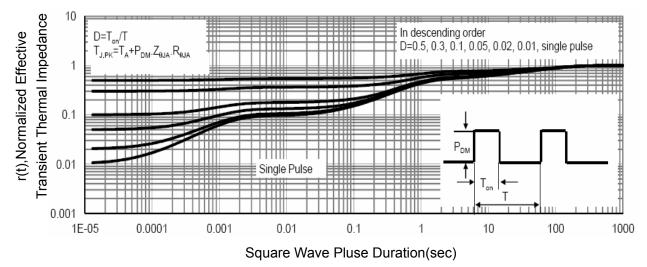
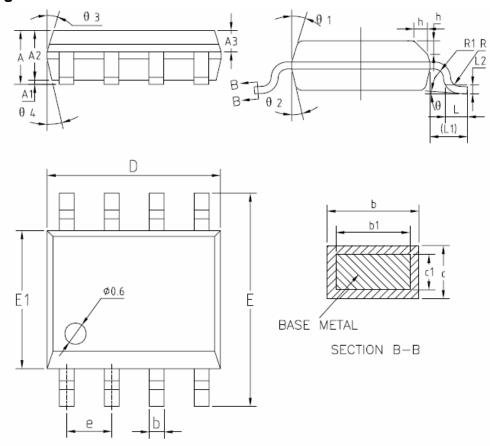


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	1.35	1.55	1.75	
A1	0.10	0.15	0.25	
A2	1.25	1.40	1.65	
A3	0.50	0.60	0.70	
b	0.38	_	0.51	
b1	0.37	0.42	0.47	
С	0.18	_	0.25	
c1	0.17	0.20	0.23	
D	4.80	4.90	5.00	
E	5.80	6.00	6.20	
E1	3.80	3.90	4.00	
е	1.17	1.27	1.37	
L	0.45	0.60	0.80	
L1	1.04REF			
L2	0.25BSC			
R	0.07	_	-	
R1	0.07	_	_	
h	0.30	0.40	0.50	
θ	0,	_	8°	
θ 1	15 °	17°	19*	
θ 2	11*	13°	15*	
θ 3	15°	17'	19"	
θ 4	11*	13°	15*	



http://www.ncepower.com

NCE30ND07BS

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